



# BUK9K18-40E

Dual N-channel 40 V, 19.5 mΩ logic level MOSFET

16 March 2016

Product data sheet

## 1. General description

Dual logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with  $V_{GS(th)}$  rating of greater than 0.5 V at 175 °C

## 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

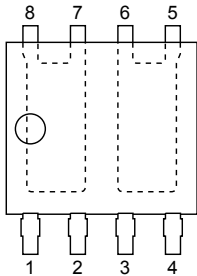
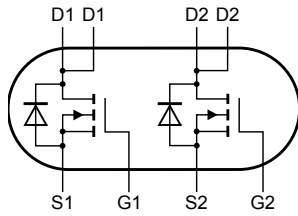
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	40	V
$I_D$	drain current	$V_{GS} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	-	-	30	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>	-	-	38	W
<b>Static characteristics FET1 and FET2</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 5\text{ V}$ ; $I_D = 10\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 12</a>	-	17.1	19.5	mΩ
<b>Dynamic characteristics FET1 and FET2</b>						
$Q_{GD}$	gate-drain charge	$I_D = 10\text{ A}$ ; $V_{DS} = 32\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 14</a>	-	3	-	nC

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	 <p>LFPAK56D (SOT1205)</p>	 <p>mbk725</p>
2	G1	gate1		
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		
7	D1	drain1		
8	D1	drain1		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9K18-40E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9K18-40E	91840E

## 8. Limiting values

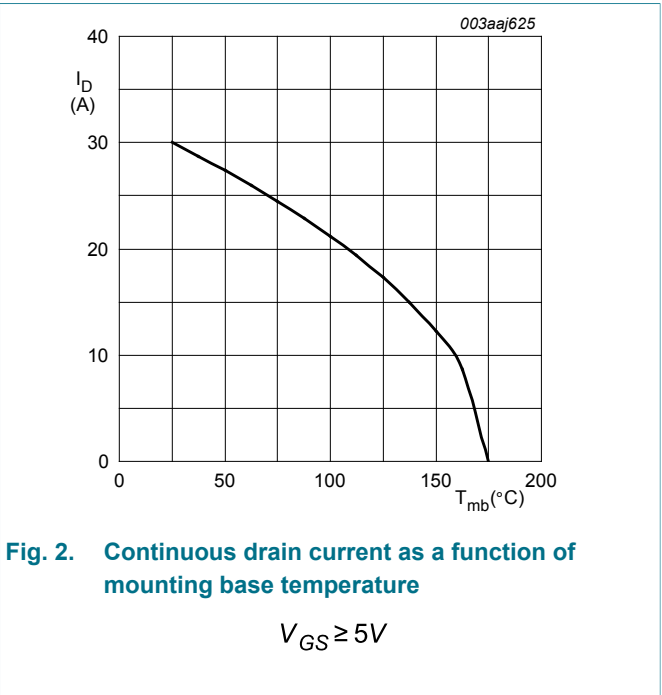
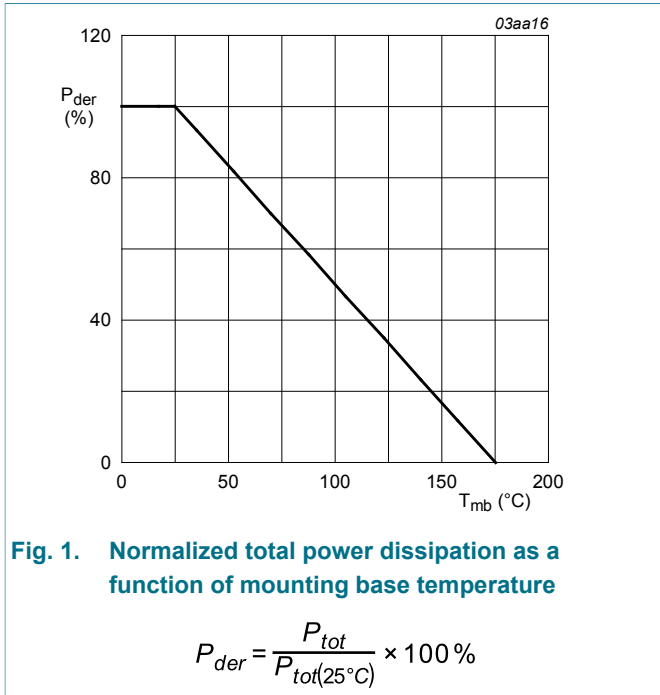
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	40	V
$V_{DGR}$	drain-gate voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	40	V
$V_{GS}$	gate-source voltage	DC; $T_j \leq 175\text{ °C}$	-10	10	V
		Pulsed; $T_j \leq 175\text{ °C}$	[1][2]	15	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; Fig. 1	-	38	W
$I_D$	drain current	$V_{GS} = 5\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; Fig. 2	-	30	A
		$V_{GS} = 5\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; Fig. 2	-	24	A

Symbol	Parameter	Conditions	Min	Max	Unit
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10 \mu\text{s}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 3</a>	-	124	A
$T_{stg}$	storage temperature		-55	175	$^\circ\text{C}$
$T_j$	junction temperature		-55	175	$^\circ\text{C}$
$T_{sl(M)}$	peak soldering temperature		-	260	$^\circ\text{C}$
<b>Source-drain diode FET1 and FET2</b>					
$I_S$	source current	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	30	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10 \mu\text{s}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	124	A
<b>Avalanche Ruggedness FET1 and FET2</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 30 \text{ A}$ ; $V_{sup} \leq 40 \text{ V}$ ; $V_{GS} = 5 \text{ V}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 4</a>	<a href="#">[3][4]</a>	-	22 mJ

- [1] Accumulated Pulse duration up to 50 hours delivers zero defect ppm
- [2] Significantly longer life times are achieved by lowering  $T_j$  and or  $V_{GS}$ .
- [3] Refer to application note AN10273 for further information
- [4] Single-pulse avalanche rating limited by maximum junction temperature of 175  $^\circ\text{C}$



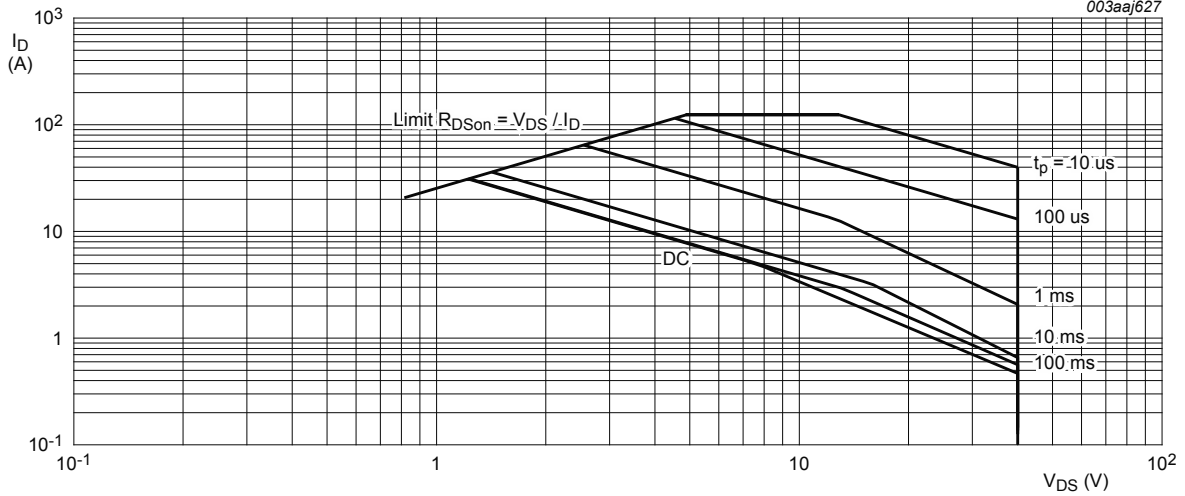


Fig. 3. Safe operating area; continuous and peak drain current as a function of drain-source voltage

$T_{mb} = 25^\circ C; I_{DM}$  is single pulse

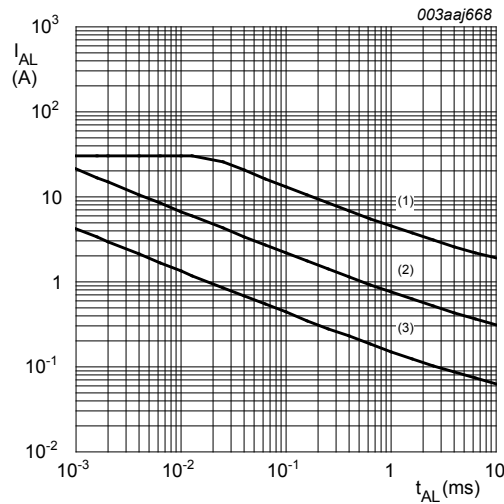


Fig. 4. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

- (1) Single-pulse;  $T_j = 25^\circ C$ .
- (2) Single-pulse;  $T_j = 150^\circ C$ .
- (3) Repetitive.

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	3.96	K/W

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

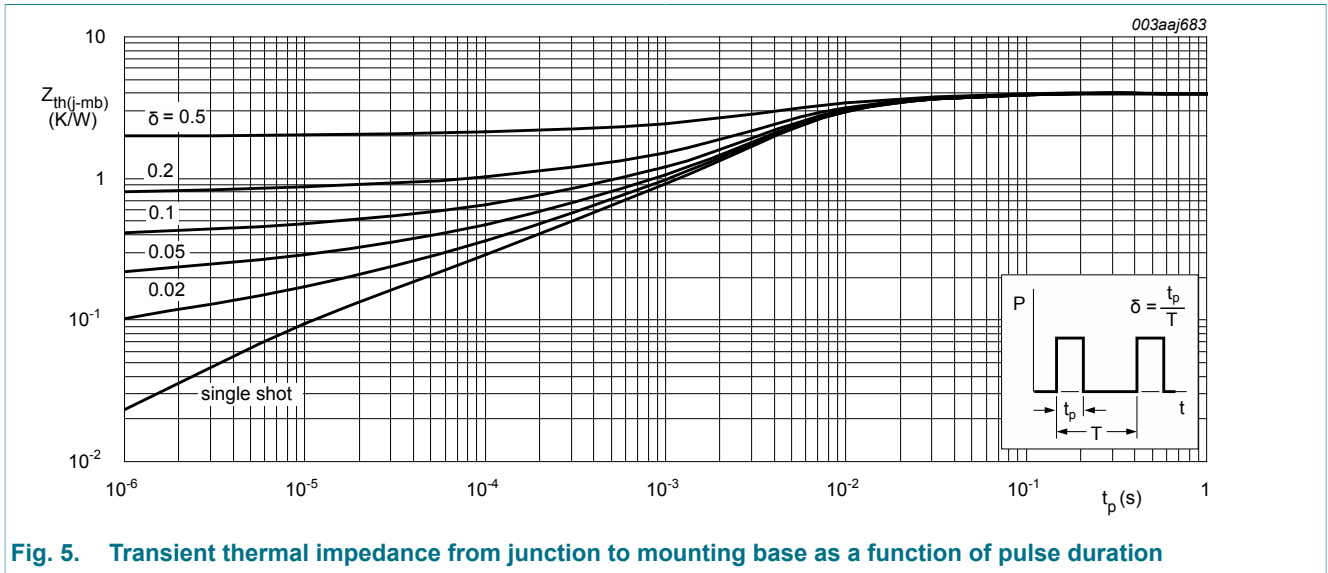


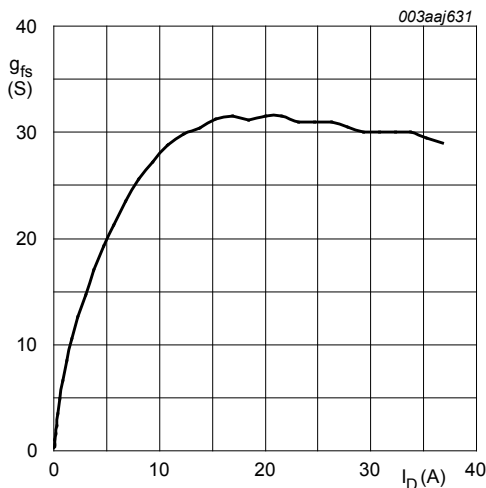
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

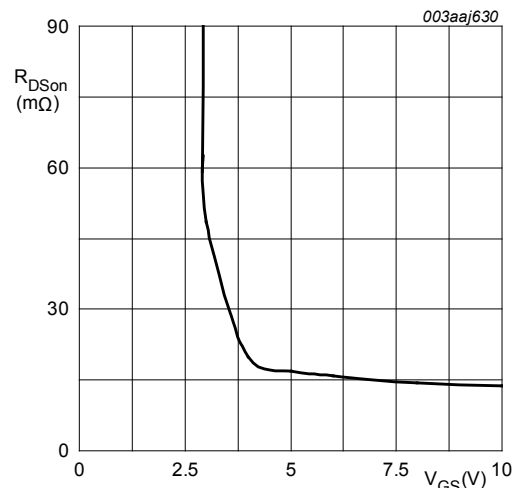
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics FET1 and FET2</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	36	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	40	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 10; Fig. 11</a>	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C;$ <a href="#">Fig. 10; Fig. 11</a>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C;$ <a href="#">Fig. 10; Fig. 11</a>	-	-	2.45	V
$I_{DSS}$	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ C$	-	-	500	$\mu A$
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	0.02	1	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ }^\circ C;$ <a href="#">Fig. 12</a>	-	17.1	19.5	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 10 \text{ A}; T_j = 175 \text{ }^\circ C;$ <a href="#">Fig. 12; Fig. 13</a>	-	34.37	39.2	mΩ

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_{GS} = 10\text{ V}; I_D = 10\text{ A}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 12</a>	-	13.5	16	mΩ
<b>Dynamic characteristics FET1 and FET2</b>						
$Q_{G(\text{tot})}$	total gate charge	$I_D = 10\text{ A}; V_{DS} = 32\text{ V}; V_{GS} = 10\text{ V};$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	-	14.5	-	nC
$Q_{GS}$	gate-source charge	$I_D = 10\text{ A}; V_{DS} = 32\text{ V}; V_{GS} = 10\text{ V};$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 14</a>	-	2	-	nC
$Q_{GD}$	gate-drain charge		-	3	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 25\text{ V}; V_{GS} = 0\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 16</a>	-	796	1061	pF
$C_{oss}$	output capacitance		-	137	164	pF
$C_{rss}$	reverse transfer capacitance		-	82	112	pF
$t_{d(\text{on})}$	turn-on delay time	$V_{DS} = 32\text{ V}; R_L = 3.3\text{ }^\Omega; V_{GS} = 10\text{ V};$ $R_{G(\text{ext})} = 5\text{ }^\Omega; T_j = 25\text{ }^\circ\text{C}$	-	4	-	ns
$t_r$	rise time		-	4.6	-	ns
$t_{d(\text{off})}$	turn-off delay time		-	17.5	-	ns
$t_f$	fall time		-	9.9	-	ns
<b>Source-drain diode FET1 and FET2</b>						
$V_{SD}$	source-drain voltage	$I_S = 10\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 17</a>	-	0.78	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 10\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 20\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	8.3	-	ns
$Q_r$	recovered charge		-	16.2	-	nC



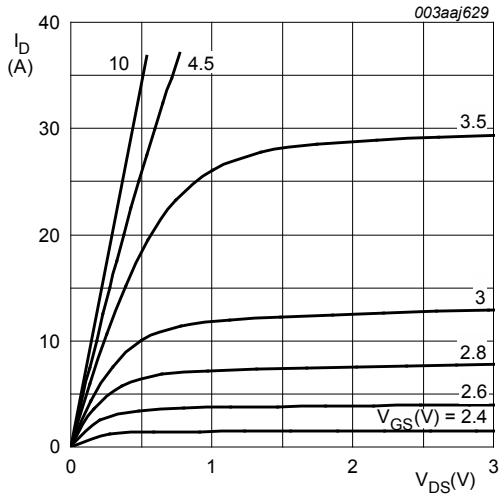
**Fig. 6. Forward transconductance as a function of drain current; typical values**

$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$



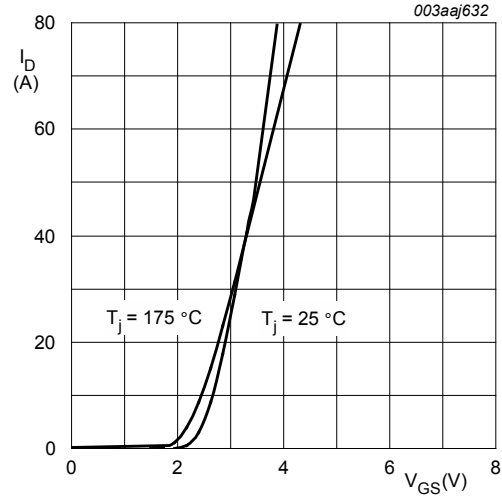
**Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values**

$T_j = 25\text{ }^\circ\text{C}; I_D = 10\text{ A}$



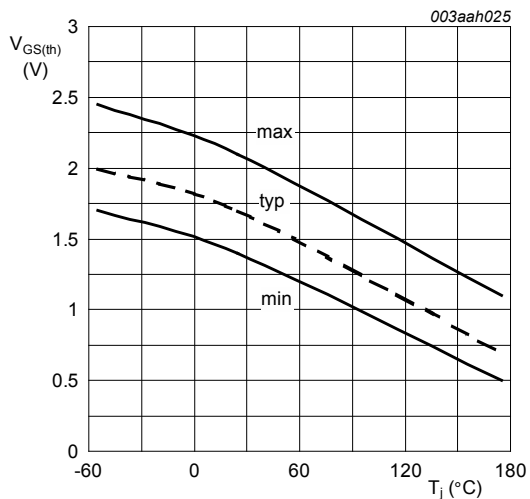
$T_j = 25\text{ }^\circ\text{C}; t_p = 300\text{ }\mu\text{s}$

**Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values**



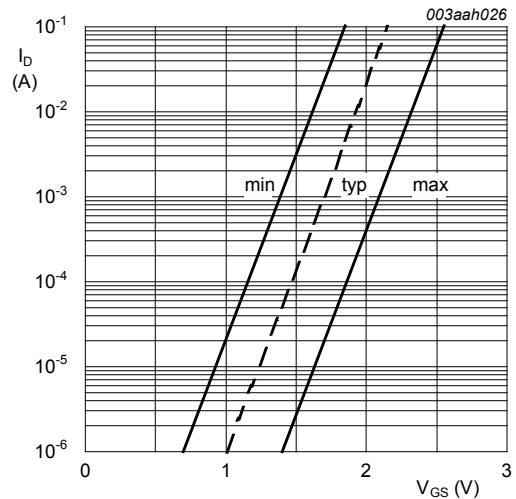
$V_{DS} = 10\text{ V}$

**Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**



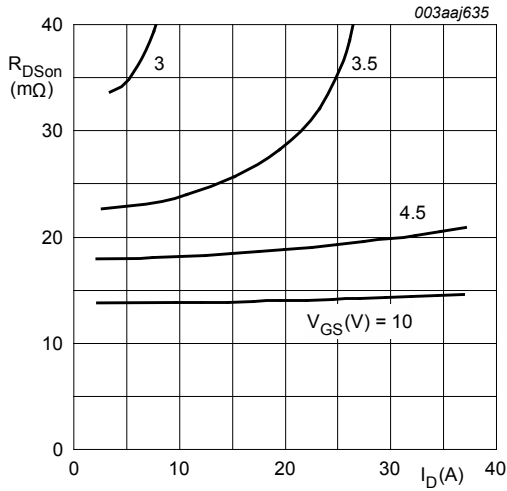
$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

**Fig. 10. Gate-source threshold voltage as a function of junction temperature**



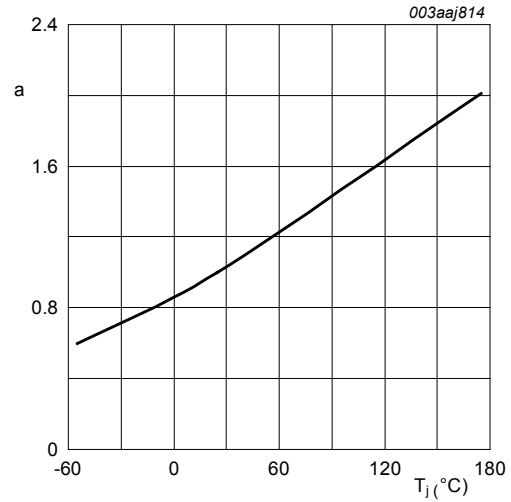
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

**Fig. 11. Sub-threshold drain current as a function of gate-source voltage**



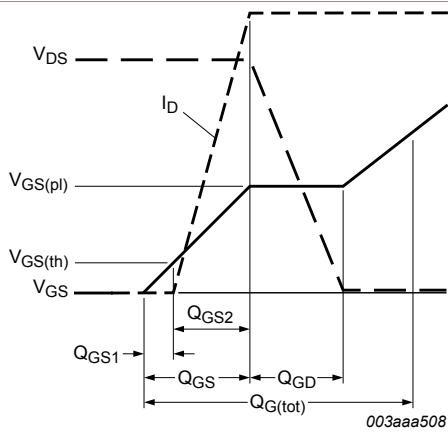
$T_j = 25\text{ }^\circ\text{C}; t_p = 300\text{ }\mu\text{s}$

**Fig. 12. Drain-source on-state resistance as a function of drain current; typical values**

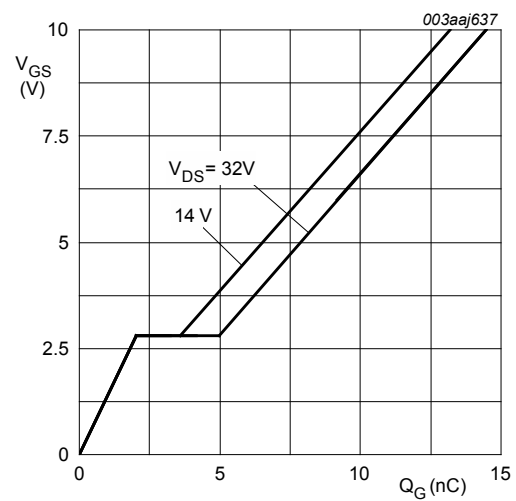


**Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature**

$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$



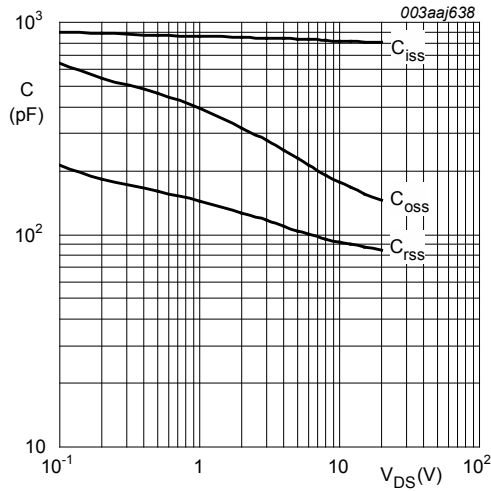
**Fig. 14. Gate charge waveform definitions**



**Fig. 15. Gate-source voltage as a function of gate charge; typical values**

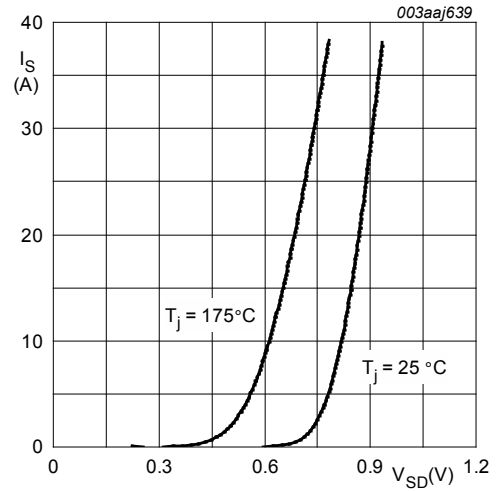
$T_j = 25\text{ }^\circ\text{C}; I_D = 10\text{ A}$





**Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**

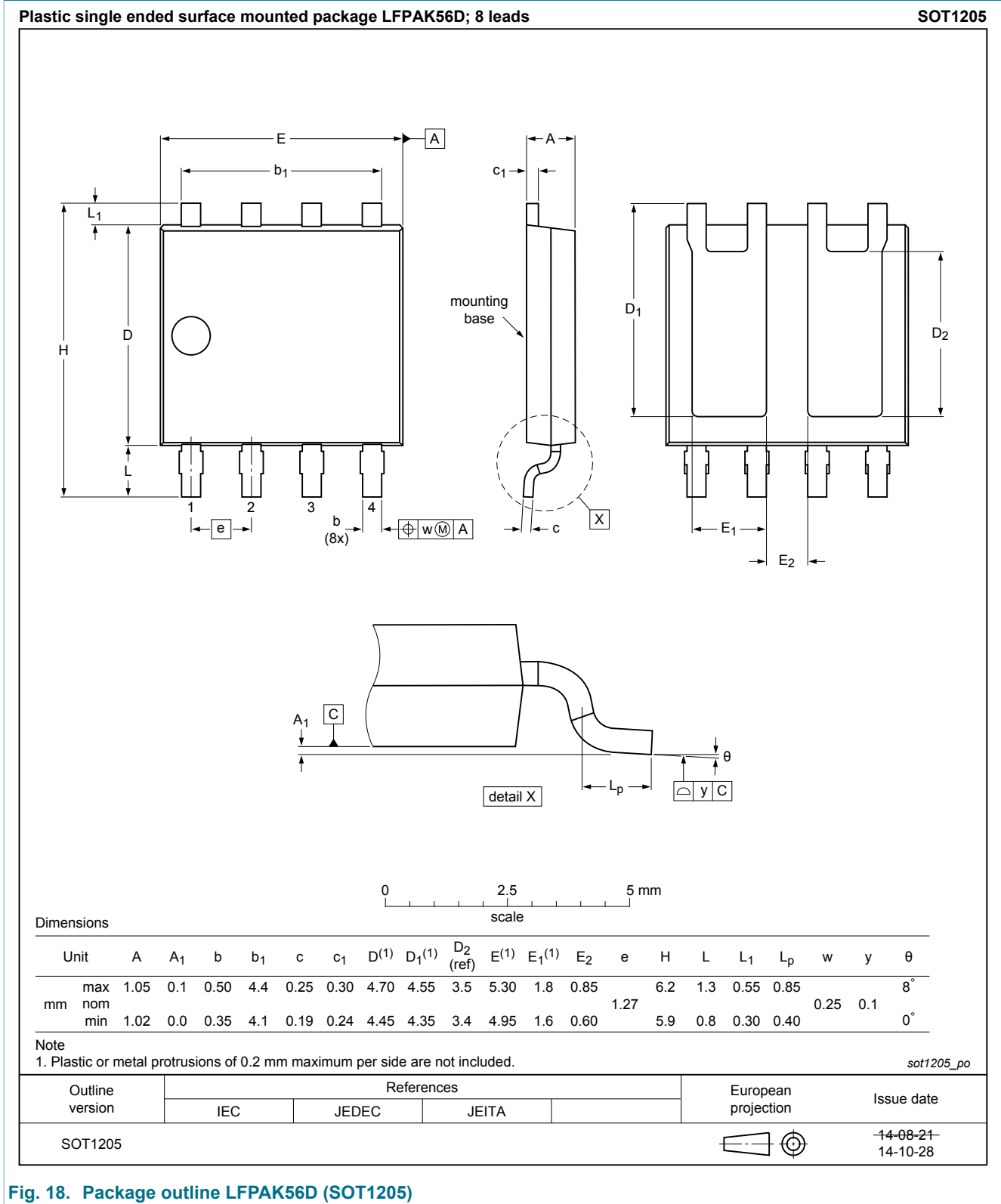
$$V_{GS} = 0V; f = 1MHz$$



**Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values**

$$V_{GS} = 0V$$

### 11. Package outline



**Fig. 18. Package outline LFAK56D (SOT1205)**

## 12. Legal information

### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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## 13. Contents

1	General description .....	1
2	Features and benefits .....	1
3	Applications .....	1
4	Quick reference data .....	1
5	Pinning information .....	2
6	Ordering information .....	2
7	Marking .....	2
8	Limiting values .....	2
9	Thermal characteristics .....	4
10	Characteristics .....	5
11	Package outline .....	10
12	Legal information .....	11
12.1	Data sheet status .....	11
12.2	Definitions .....	11
12.3	Disclaimers .....	11
12.4	Trademarks .....	12

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